

• This device is available in Pb-free package(s). Specifications herein apply to both standard and Pb-free devices. Please see our website at www.onsemi.com for specific Pb-free orderable part numbers, or contact your local ON Semiconductor sales office or representative.

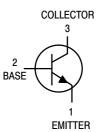
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	15	Vdc
Collector – Emitter Voltage	V _{CES}	40	Vdc
Collector – Base Voltage	V _{CBO}	40	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current — Continuous — 10 µs Pulse	Ι _C	300 500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C



ON Semiconductor Preferred Device





THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	R _{θJA}	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage	$(I_{C} = 100 \ \mu Adc, \ V_{BE} = 0)$	V _{(BR)CES}	40	—	Vdc
Collector – Emitter Sustaining Voltage ⁽¹⁾	(I _C = 10 mAdc, I _B = 0)	V _{CEO(sus)}	15	—	Vdc
Collector – Base Breakdown Voltage	$(I_{C} = 100 \ \mu Adc, I_{E} = 0)$	V _{(BR)CBO}	40	—	Vdc
Emitter – Base Breakdown Voltage	$(I_E = 100 \ \mu Adc, \ I_C = 0)$	V _{(BR)EBO}	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 20 \text{ Vdc}, V_{BE} = 0$) ($V_{CE} = 20 \text{ Vdc}, V_{BE} = 0, T_A = 65^{\circ}\text{C}$)		I _{CES}		0.5 3.0	μAdc

ON CHARACTERISTICS(1)

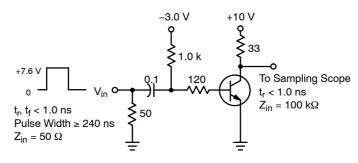
DC Current Gain	$(I_{C} = 30 \text{ mAdc}, V_{CE} = 0.4 \text{ Vdc})$ $(I_{C} = 100 \text{ mAdc}, V_{CE} = 0.5 \text{ Vdc})$ $(I_{C} = 300 \text{ mA}, V_{CE} = 1.0 \text{ Vdc})$	h _{FE}	30 25 15	120 	—
Collector – Emitter Saturation Voltage		V _{CE(sat)}		0.2 0.28 0.5 0.3	Vdc
Base – Emitter Saturation Voltage	(I _C = 30 mAdc, I _B = 3.0 mAdc) (I _C = 100 mAdc, I _B = 10 mAdc) (I _C = 300 mAdc, I _B = 30 mA)	V _{BE(sat)}	0.73 — —	0.95 1.2 1.7	Vdc

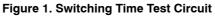
1. Pulse Test: Pulse Width \leq 300 µs; Duty Cycle \leq 2.0%.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T _A =	25°C unless otherwise noted) (Continued)
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	Symbol	Min	Max	Unit	
SMALL-SIGNAL	CHARACTERISTICS	L	L		
Current – Gain — E (I _C = 30 mAdc, V	Bandwidth Product / _{CE} = 10 Vdc, f = 100 MHz)	f _T	350	_	MHz
Output Capacitanc (V _{CB} = 5.0 Vdc,	e I _E = 0, f = 1.0 MHz)	C _{obo}		5.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}		9.0	pF
	ARACTERISTICS	·			
Turn-On Time		t _{on}	—	18	ns
Delay Time	(V _{CC} = 10 Vdc, I _C = 300 mAdc, I _{B1} = 30 mAdc) (Figure 1)	t _d	—	10	ns
Rise Time		t _r	—	15	ns
Turn-Off Time	(V _{CC} = 10 Vdc, I _C = 300 mAdc, I _{B1} = I _{B2} = 30 mAdc)	t _{off}	—	28	ns
Fall Time	(Figure 1)	t _f		15	ns
Storage Time (V _{CC} = 10 Vdc, I _C = 10 mAdc, I _{B1} = I _{B2} = 10 mAdc) (Figure 2)		t _s	—	18	ns





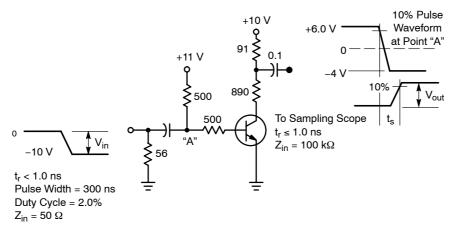
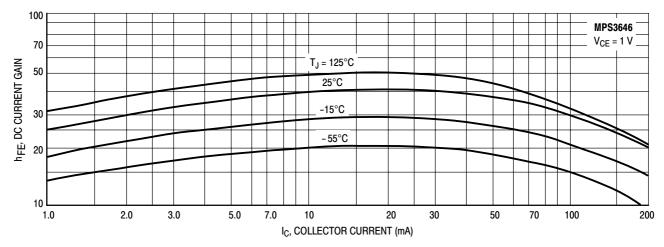
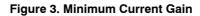


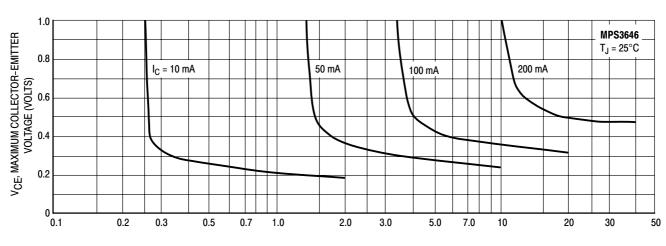
Figure 2. Charge Storage Time Test Circuit

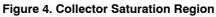
CURRENT GAIN CHARACTERISTICS

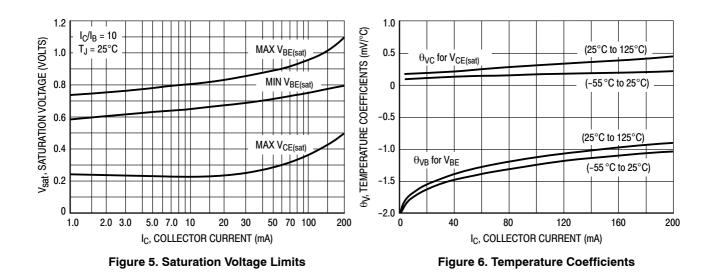




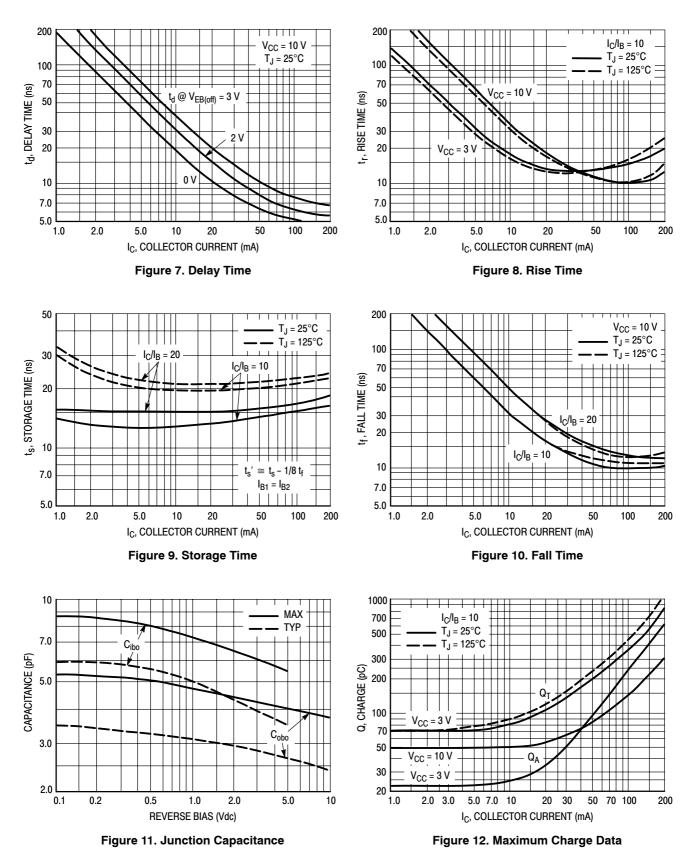
"ON" CONDITION CHARACTERISTICS





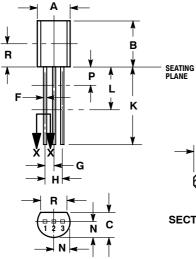


DYNAMIC CHARACTERISTICS



PACKAGE DIMENSIONS

CASE 029-11 (TO-226AA) ISSUE AD









NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. 4. DIMENSION F APPLIES BETWEEN P AND L DIMENSIONS D AND J APPLY BETWEEN L AND K MIMIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.135		3.43	

<u>Notes</u>

<u>Notes</u>

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